



## Future Normal in Semiconductor

2025년 2월 14일(금), 09:00-10:45

Room H(루비 I), 5층

### F. Silicon and Group-IV Devices and Integration Technology 분과

#### O48\_[FH1-F] 3D GAA/CFET Technology

좌장: 정규원 교수(서울대학교), 김시현 교수(서강대학교)

<p>FH1-F-1 09:00-09:15</p>	<p><b>Low-Temperature Fabrication of Silicon Nanowire GAAFETs with Excimer Laser Recrystallization for M3D Integration</b> Jeong Yeon Im<sup>1</sup>, Hanbin Lee<sup>1</sup>, Gyeongsu Min<sup>1</sup>, Hyo-In Yang<sup>1</sup>, So Jeong Park<sup>1</sup>, Jun-Ho Jang<sup>1</sup>, Ji Won Park<sup>1</sup>, Seonghyeon Jeong<sup>1</sup>, Dae Hwan Kim<sup>1</sup>, Jong-Ho Bae<sup>1</sup>, Dong Myong Kim<sup>3</sup>, Min-Ho Kang<sup>2</sup>, and Sung-Jin Choi<sup>1</sup> <sup>1</sup>School of Electrical Engineering, Kookmin University, <sup>2</sup>Department of Nano-process, National Nanofab Center, <sup>3</sup>Department of Advanced Technology, DGIST</p>
<p>FH1-F-2 09:15-09:30</p>	<p><b>Strained Ge/Si Heterogeneous 3D Sequential CFET Featuring First Strain Engineered Ge Top Channel</b> Hyeonrak Lim<sup>1</sup>, Seong Kwang Kim<sup>1</sup>, Seung Woo Lee<sup>1</sup>, Youngkeun Park<sup>1</sup>, Jaejoong Jeong<sup>1</sup>, Hojin Jeong<sup>1</sup>, Jinha Lim<sup>1</sup>, Dae-Myeong Geum<sup>2</sup>, Jaehoon Han<sup>3</sup>, Younghyun Kim<sup>4</sup>, Jaeyong Jeong<sup>1</sup>, Byung Jin Cho<sup>1</sup>, and Sanghyeon Kim<sup>1</sup> <sup>1</sup>KAIST, <sup>2</sup>Inha University, <sup>3</sup>KIST, <sup>4</sup>Hanyang University</p>
<p>FH1-F-3 09:30-09:45</p>	<p><b>Photoresponsive GIDL Characterization for Simultaneous Extraction of Donor- and Acceptor-like Interface Trap States in Vertically Stacked Si-NW GAA FETs</b> Seohyeon Park<sup>1</sup>, Donghyeon Lee<sup>1</sup>, Jaewook Yoo<sup>1</sup>, Minah Park<sup>1</sup>, Hongseung Lee<sup>1</sup>, Hyeonjun Song<sup>1</sup>, Soyeon Kim<sup>1</sup>, Seongbin Lim<sup>1</sup>, Sojin Jung<sup>1</sup>, TaeWan Kim<sup>3</sup>, Yang Kyu Choi<sup>2</sup>, and Hagyoul Bae<sup>1</sup> <sup>1</sup>Jeonbuk National University, <sup>2</sup>KAIST, <sup>3</sup>University of Seoul</p>
<p>FH1-F-4 09:45-10:00</p>	<p><b>Transient Analysis of CFET Inverter with Backside Interconnections : Buried Power Rails, Bottom Contacts</b> Seung-Woo Jung and Sung-Min Hong School of Electrical Engineering and Computer Science, GIST</p>



# 제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

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<p>FH1-F-5 10:00-10:15</p>	<p><b>Implementation of a Stress Calculation Module in an In-House Process Emulator for Monolithic CFET</b> Min-Seo Jang<sup>1</sup>, In Ki Kim<sup>1</sup>, Seung-Woo Jung<sup>1</sup>, Jeong Hyeon Yun<sup>2</sup>, Myoung Jin Lee<sup>2</sup>, and Sung-Min Hong<sup>1</sup> <sup>1</sup>School of Electrical Engineering and Computer Science, GIST, <sup>2</sup>Department of Electronic Engineering, Chonnam National University</p>
<p>FH1-F-6 10:15-10:30</p>	<p><b>A Novel 3D-SRAM Architecture based on VGAA Transistors for Advanced AI and Edge Computing Applications</b> Changwoo Han and Changhwan Shin School of Electrical Engineering, College of Engineering, Korea University</p>
<p>FH1-F-7 10:30-10:45</p>	<p><b>Multi-<math>V_{th}</math> Through Different Inner Gates Work Functions</b> Seungjoon Jeong, Haevin Choi, and Changhwan Shin School of Electrical Engineering, Korea University</p>